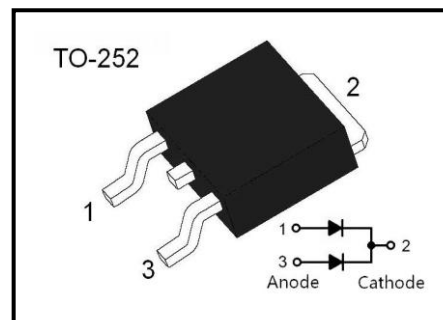


Schottky Barrier Rectifier Diodes

Features:

- Average Output Rectified Current : $I_O = 10A$.
- Repetitive Peak Reverse Voltage : $V_{RRM} = 200V$
- Guard Ring Die Construction for Transient Protection.
- High Surge Current Capability.
- Low Forward Voltage Drop.



Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Units
Peak Inverse Voltage	V_{RRM}	200	V
RMS reverse voltage	$V_{R(RMS)}$	140	V
Average rectified output current@ $T_c=100^\circ C$	I_O	10	A
Nonrepetitive Peak Surge Current@8.3ms	$I_{F(SM)}$	100	A
Operating Junction Temperature	T_J	125	$^\circ C$
Storage Temperature	T_{STG}	-55~+150	$^\circ C$

Electrical Characteristics ($T_A = 25^\circ C$ unless otherwise noted)

Test Condition	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Reverse Breakdown Voltage	V_{BR}	$I_R = 0.1mA$	200			V
Reverse Leakage Current	I_R	$V_R = 200V$			0.1	mA
Forward Voltage	V_{F1}	$I_F = 5A$			0.9	V
	$V_{F(2)}^*$	$I_F = 10A$			1.0	
Typical total capacitance	C_{tot}	$V_R = 4V, f = 1MHz$			500	pF

*Pulse test

Typical Characteristics

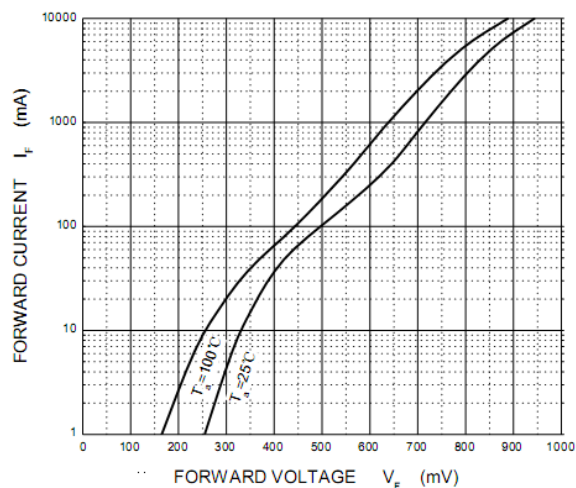


Figure 1. Forward Characteristics

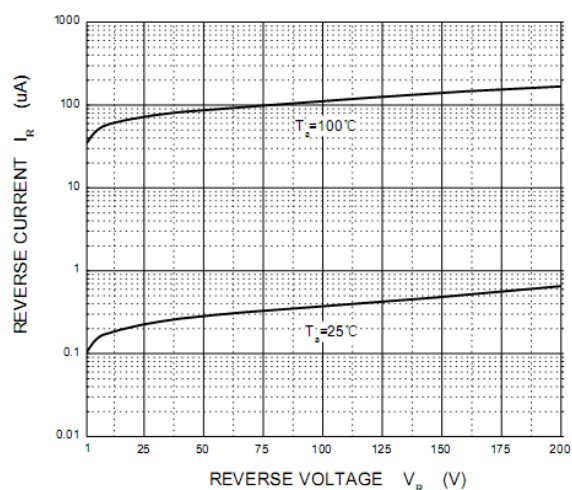


Figure 2. Reverse Characteristics

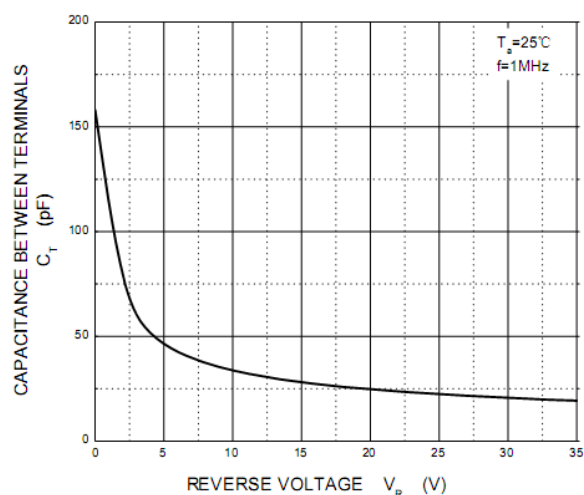


Figure 3. Capacitance Characteristics

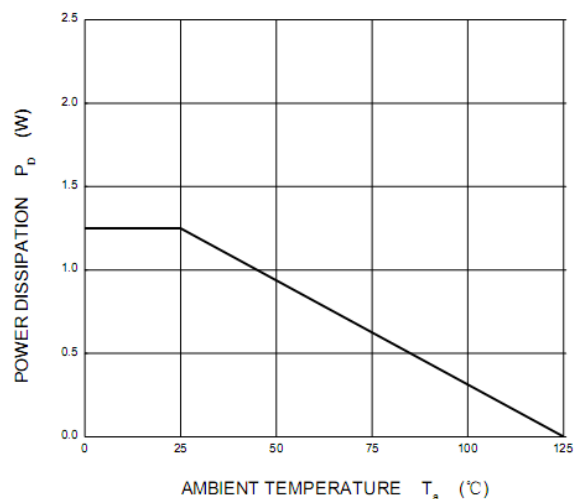
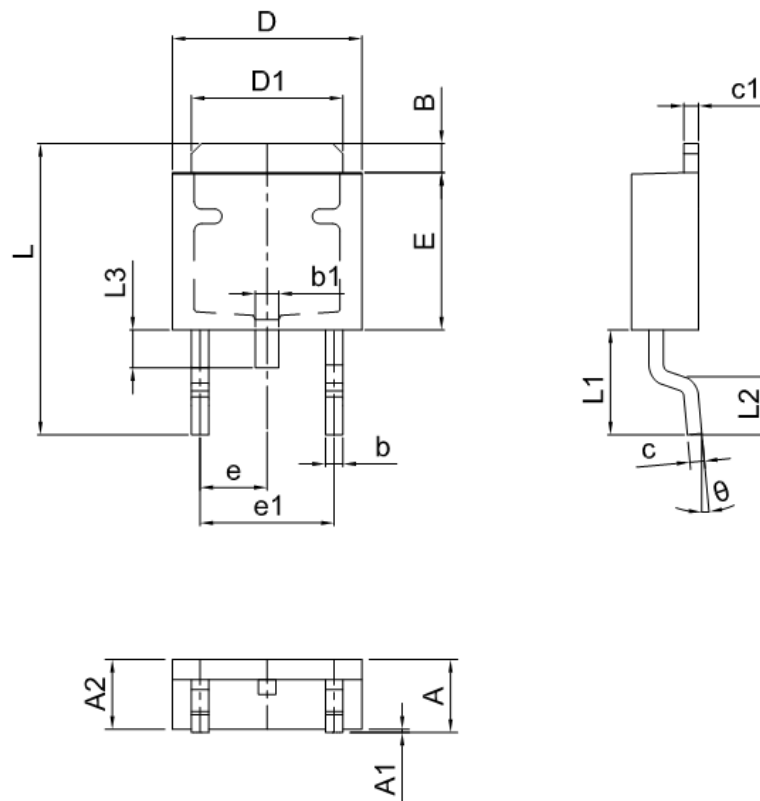


Figure 4. Power Derating Curve

Package Dimensions (Unit:mm)



Symbol	Min.	Typ	Max.
A	2.20	2.35	2.50
A1	0.00	0.05	0.12
A2	2.20	2.30	2.40
B	1.20	1.40	1.60
b	0.50	0.60	0.70
b1	0.70	0.80	0.90
c	0.40	0.50	0.60
c1	0.40	0.50	0.60
D	6.35	6.50	6.65
D1	5.20	5.30	5.40
E	5.40	5.50	5.70
e	2.20	2.30	2.40
e1	4.40	4.60	4.80
L	9.60	9.90	10.20
L1	2.70	2.90	3.10
L2	1.40	1.60	1.80
L3	0.90	1.20	1.50
θ	0°	4°	8°